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FDP12N50NZ / FDPF12N50NZ N-Channel UniFETTM II MOSFET 500 V, 11.5 A, 520 m Ω

Features

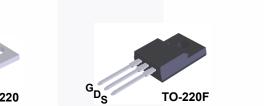
- $R_{DS(on)}$ = 460 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 5.75 A
- Low Gate Charge (Typ. 23 nC)
- Low C_{rss} (Typ. 14 pF)
- 100% Avalanche Tested
- ESD Improved Capability
- RoHS Compliant

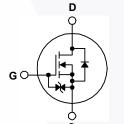
Applications

- LCD/LED/PDP TV
- Lighting
- Uninterruptible Power Supply

Description

UniFETTM II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp balasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

TO-220

Symbol	Parameter		FDP12N50NZ	FDPF12N50NZ	Unit	
V _{DSS}	Drain to Source Voltage			500		V
V _{GSS}	Gate to Source Voltage			±25		V
ID	Drain Current	- Continuous (T _C = 25 ^o C)		11.5	11.5*	A
		- Continuous ($T_c = 100^{\circ}C$)		6.9	6.9*	
I _{DM}	Drain Current	- Pulsed	(Note 1)	46	46*	А
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	560		mJ
I _{AR}	Avalanche Current		(Note 1)	11.5		А
E _{AR}	Repetitive Avalanche Energy		(Note 1)	17		mJ
dv/dt	MOSFET dv/dt Ruggedness			20		V/ns
uv/ut	Peak Diode Recovery dv/dt		(Note 3)	10		V/ns
P _D	Power Dissipation	(T _C = 25 ^o C)		170	42	W
		- Derate above 25°C		1.37	0.33	W/ºC
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300		°C	

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FDP12N50NZ	FDPF12N50NZ	Unit	
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.73	3.0	°C/W	
R_{\thetaJA}	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	-0/00	

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August 2016

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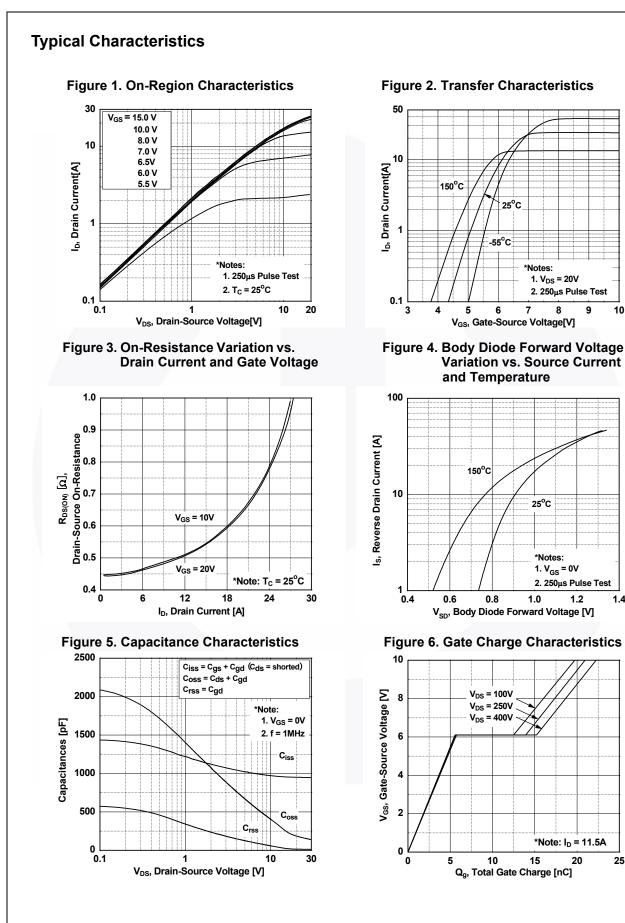
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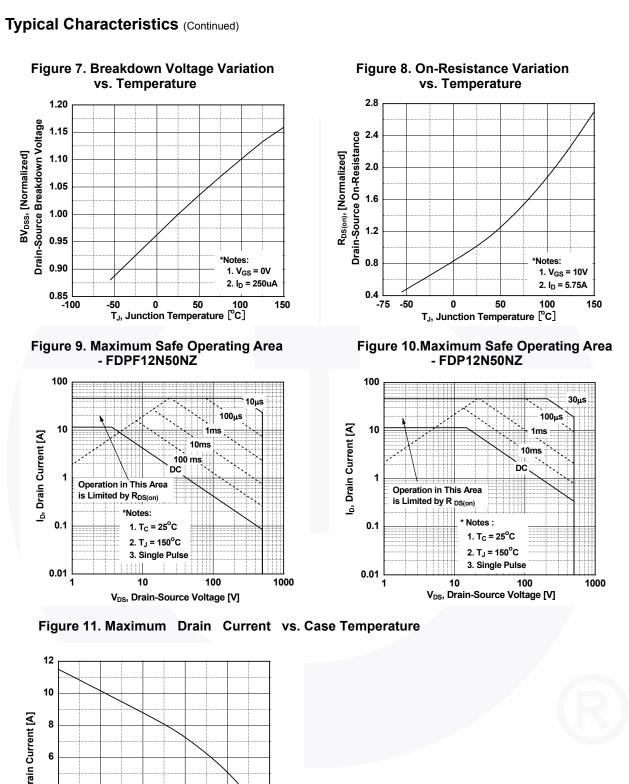
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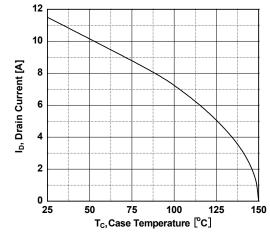
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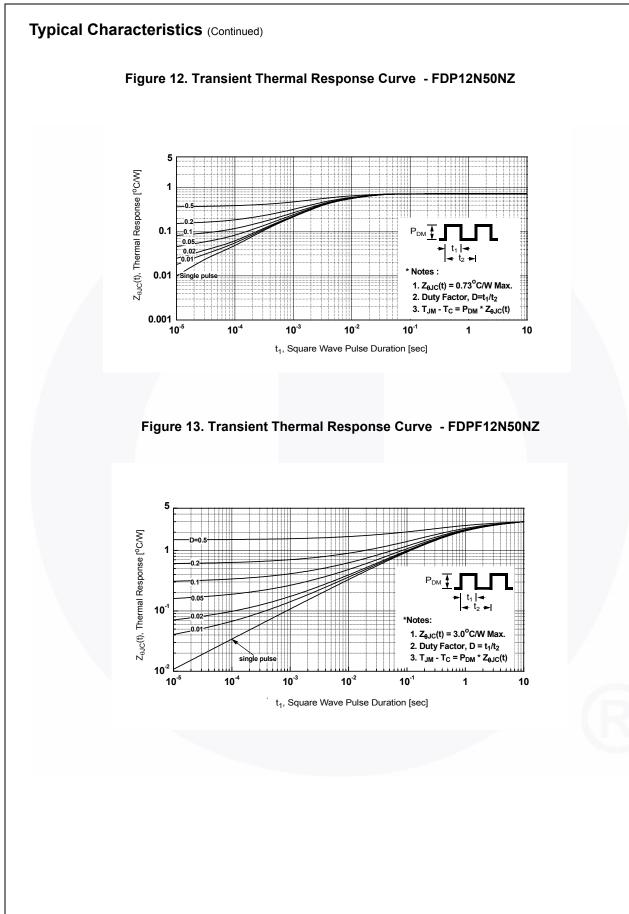


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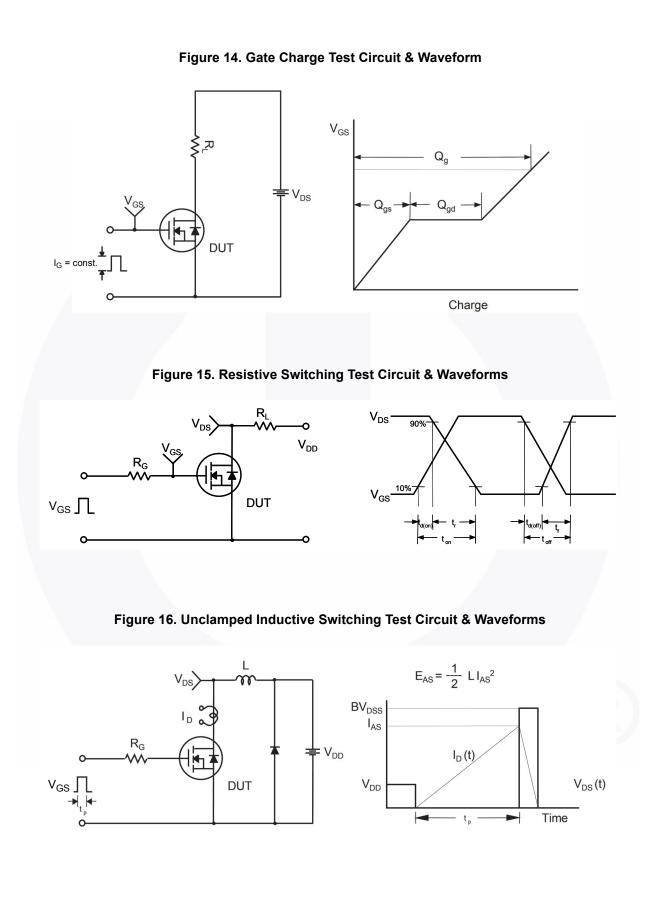




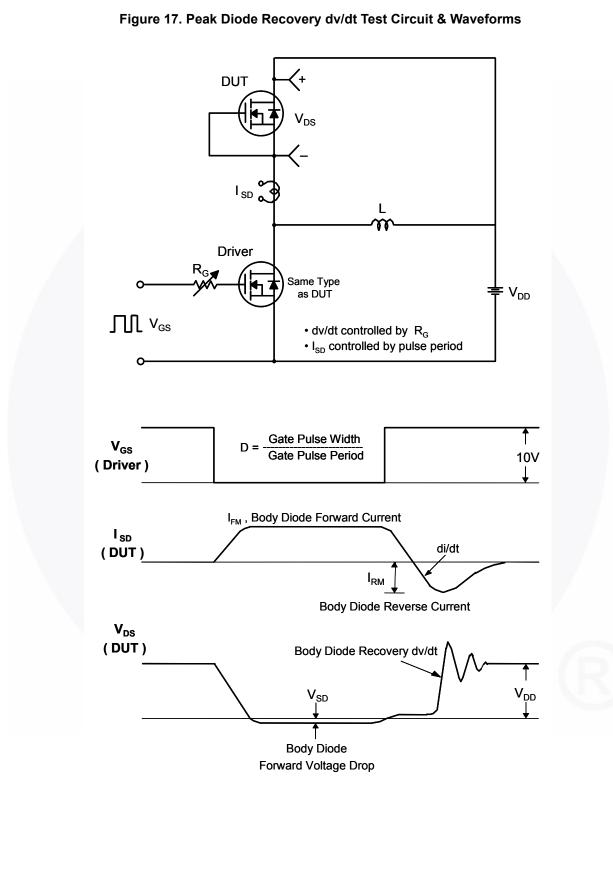
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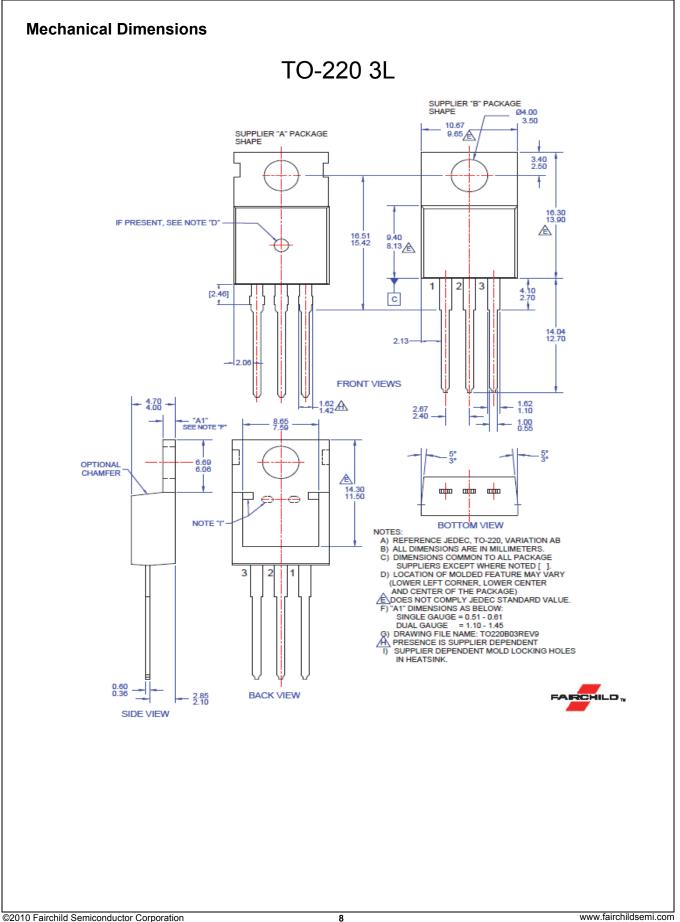
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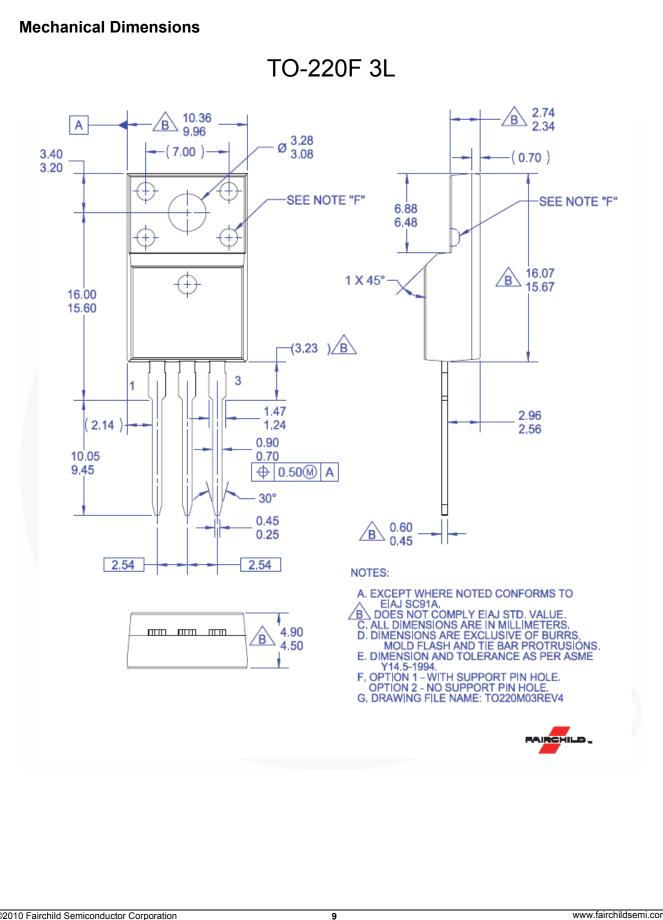


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FDP12N50NZ / FDPF12N50NZ — N-Channel UniFETTM II MOSFET







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